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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8347zuajdb

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8347EA for the 3.3-V signals, respectively.

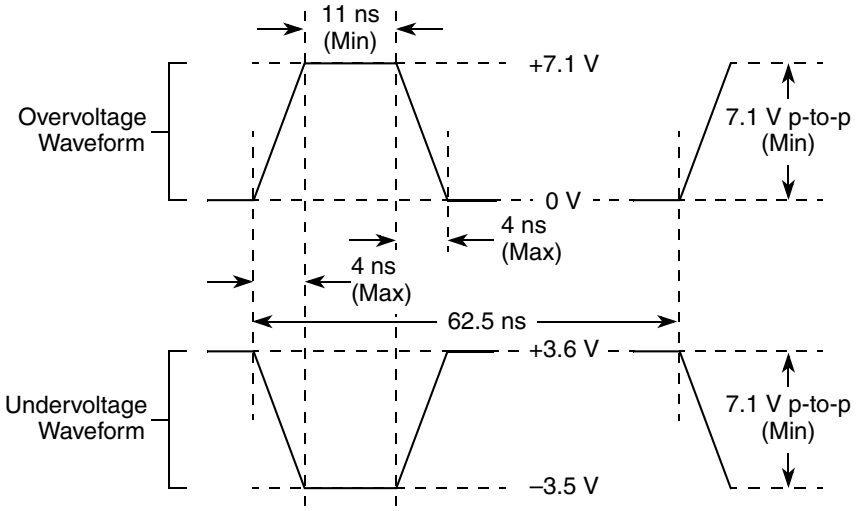


Figure 3. Maximum AC Waveforms on PCI Interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	40	OV_{DD} = 3.3 V
PCI signals (not including PCI output clocks)	25	
PCI output clocks (including PCI_SYNC_OUT)	40	
DDR signal	18	GV_{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)	GV_{DD} = 1.8 V
TSEC/10/100 signals	40	LV_{DD} = 2.5/3.3 V
DUART, system control, I^2C, JTAG, USB	40	OV_{DD} = 3.3 V
GPIO signals	40	OV_{DD} = 3.3 V, LV_{DD} = 2.5/3.3 V

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8347EA.

2.2.1 Power-Up Sequencing

MPC8347EAdoes not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power

supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

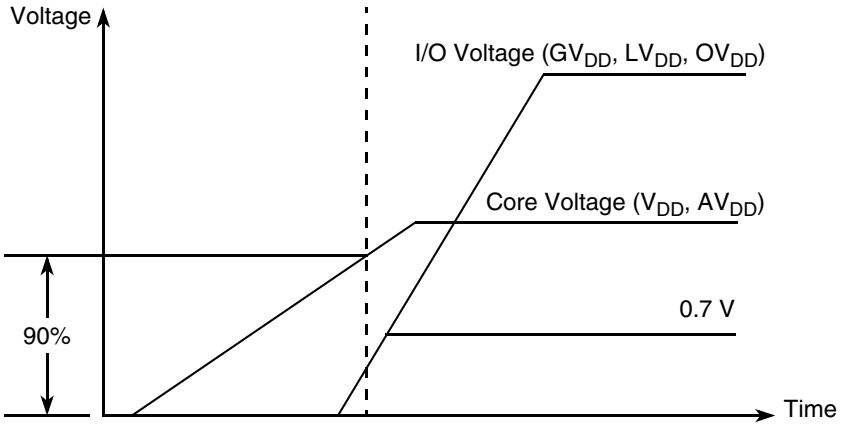


Figure 4. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

3 Power Characteristics

The estimated typical power dissipation for the MPC8347EA device is shown in Table 4.

Table 4. MPC8347EA Power Dissipation[1]

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T_J = 65	Typical[2,3]	Maximum[4]	Unit
PBGA	266	266	1.3	1.6	1.8	W
		133	1.1	1.4	1.6	W
	400	266	1.5	1.9	2.1	W
		133	1.4	1.7	1.9	W
	400	200	1.5	1.8	2.0	W
		100	1.3	1.7	1.9	W

Table 19 provides the input AC timing specifications for the DDR SDRAM interface.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC/MDM	t_{CISKEW}			ps	1, 2
400 MHz		–600	600		3
333 MHz		–750	750		—
266 MHz		–750	750		—
200 MHz		–750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: $t_{DISKEW} = \pm (T/4 - abs(t_{CISKEW}))$; where T is the clock period and abs (t_{CISKEW}) is the absolute value of t_{CISKEW}.
3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

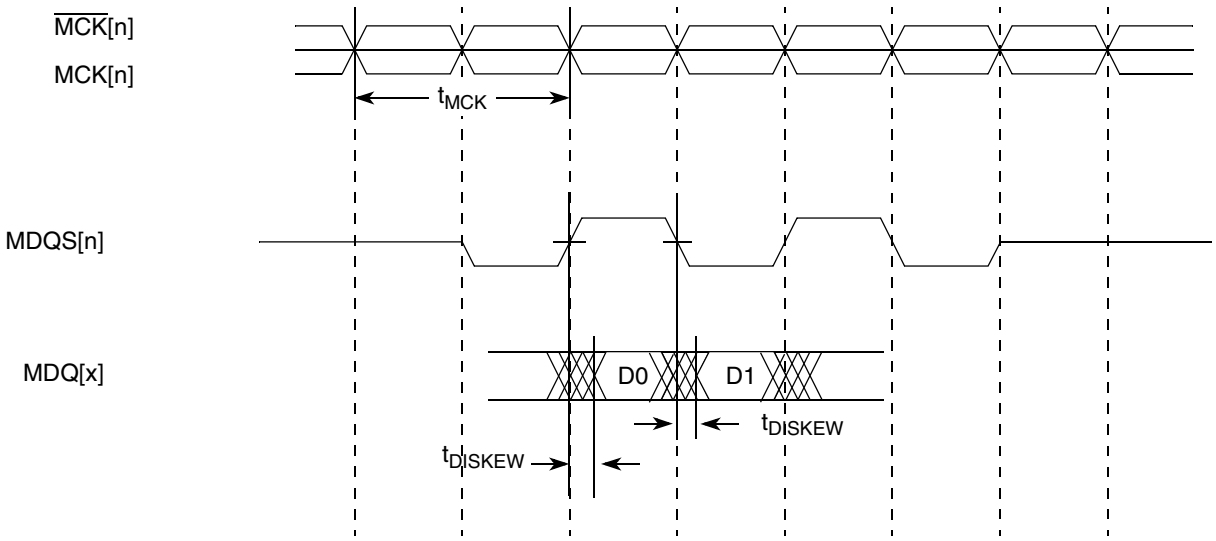


Figure 5. DDR Input Timing Diagram

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
266 MHz		1100	—		
200 MHz		1200	—		
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output goes invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are set up (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
4. t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register and is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters are set to the same adjustment value. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual* for the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK(n) at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 6 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

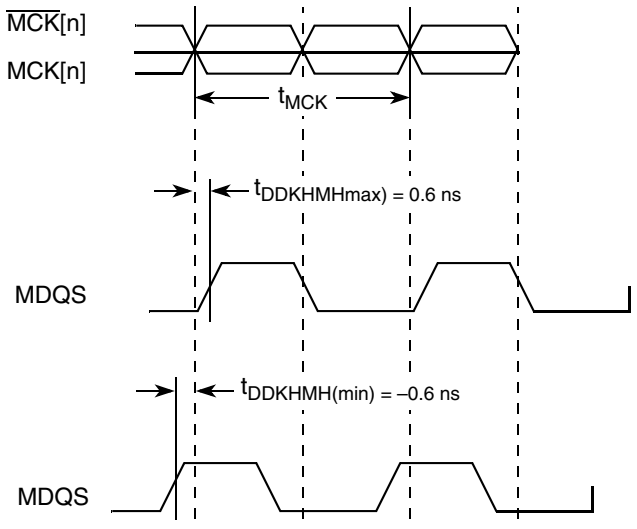


Figure 6. Timing Diagram for t_{DDKHMH}

Figure 7 shows the DDR SDRAM output timing diagram.

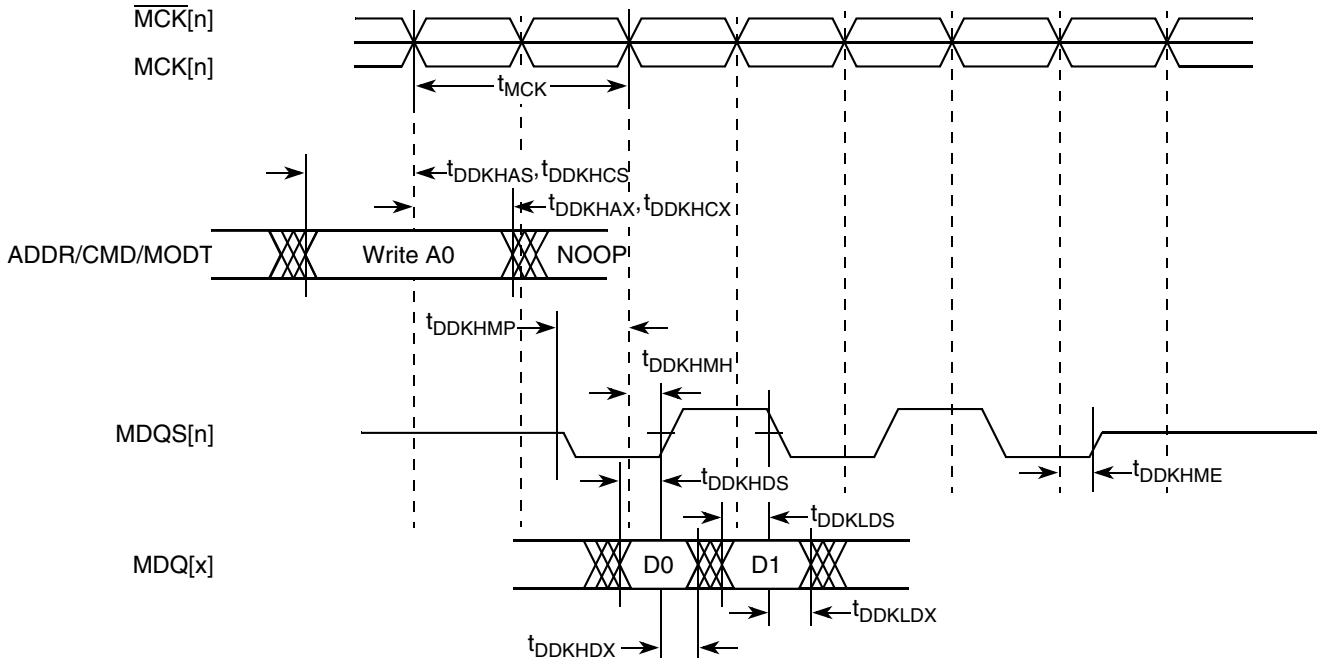


Figure 7. DDR SDRAM Output Timing Diagram

Figure 8 provides the AC test load for the DDR bus.

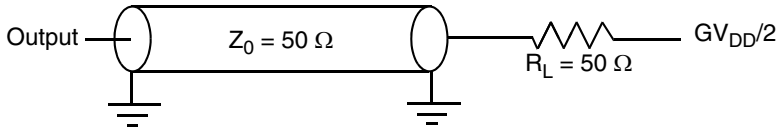


Figure 8. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8347EA.

7.1 DUART DC Electrical Characteristics

Table 21 provides the DC electrical characteristics for the DUART interface of the MPC8347EA.

Table 21. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (0.8 V ≤ V_{IN} ≤ 2 V)	I_{IN}	—	±5	μA

Table 27. MII Transmit AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 shows the MII transmit AC timing diagram.

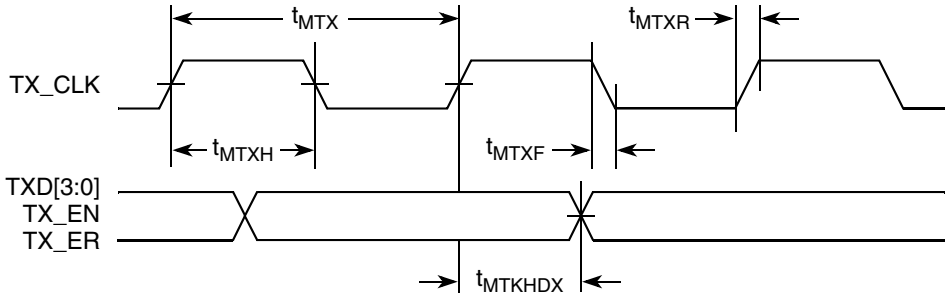


Figure 11. MII Transmit AC Timing Diagram

8.2.2.2 MII Receive AC Timing Specifications

Table 28 provides the MII receive AC timing specifications.

Table 28. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns

9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8347EA.

9.1 USB DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the USB interface.

Table 35. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

9.2 USB AC Electrical Specifications

Table 36 describes the general timing parameters of the USB interface of the MPC8347EA.

Table 36. USB General Timing Parameters (ULPI Mode Only)

Parameter	Symbol[1]	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	15	—	ns	2–5
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	2–5
Input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	2–5
USB clock to output valid—all outputs	t_{USKHOV}	—	7	ns	2–5
Output hold from USB clock—all outputs	t_{USKHOX}	2	—	ns	2–5

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to USB clock.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to 0.4 × OV_{DD} of the signal in question for 3.3 V signaling levels.
4. Input timings are measured at the pin.
5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

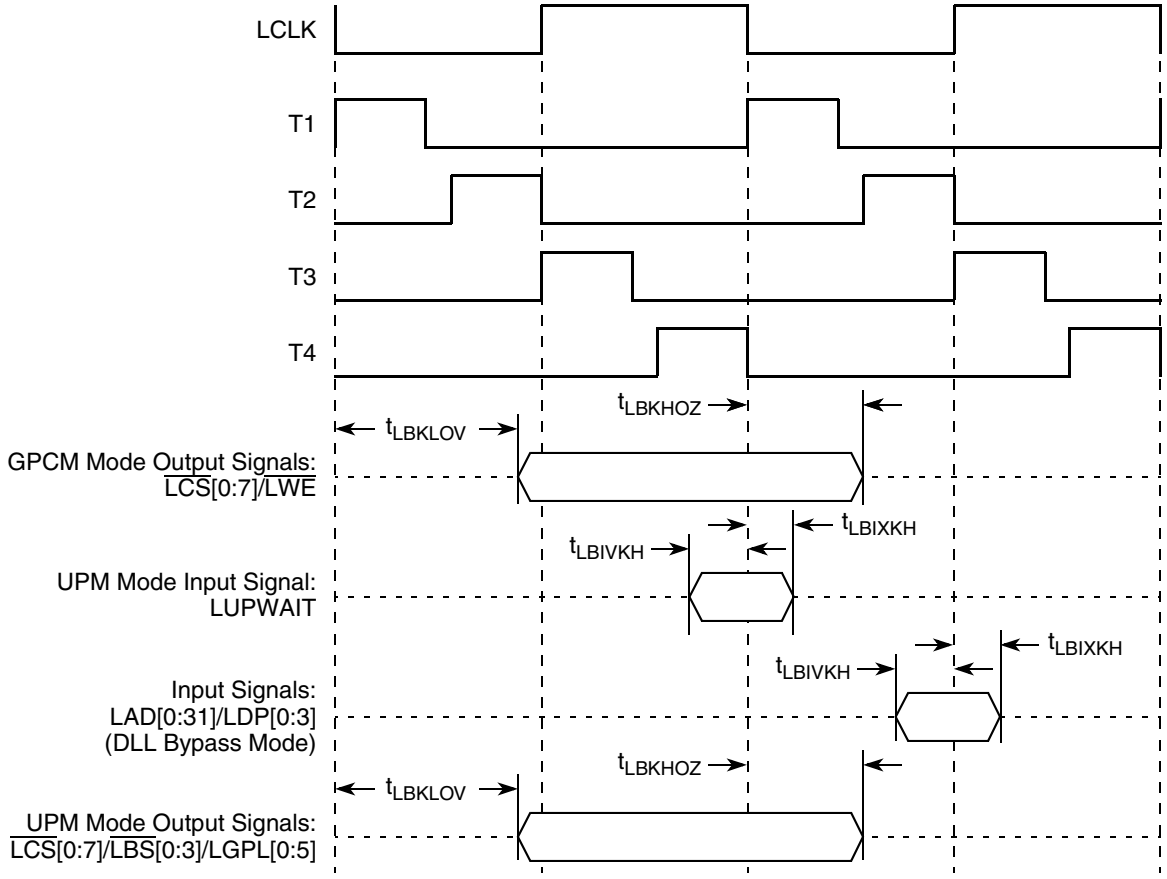


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)

12 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8347EA.

12.1 I²C DC Electrical Characteristics

Table 42 provides the DC electrical characteristics for the I²C interface of the MPC8347EA.

Table 42. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8349EA Integrated Host Processor Family Reference Manual,* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I²C AC Electrical Specifications

Table 43 provides the AC timing parameters for the I²C interface of the MPC8347EA. Note that all values refer to V_{IH}(min) and V_{IL}(max) levels (see Table 42).

Table 43. I²C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time:CBUS compatible masters I²C bus devices	t_{I2DXKL}	— 0[2]	— 0.9[3]	μs

Figure 35 shows the PCI input AC timing diagram.

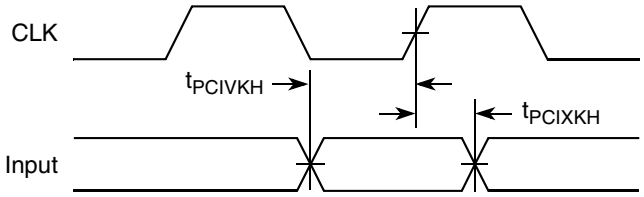


Figure 35. PCI Input AC Timing Diagram

Figure 36 shows the PCI output AC timing diagram.

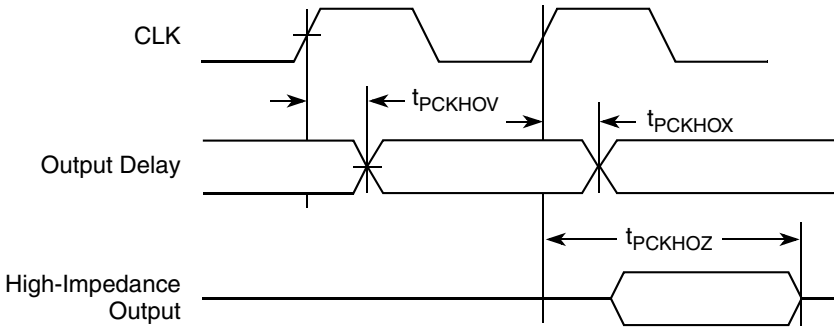


Figure 36. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 47 provides the DC electrical characteristics for the MPC8347EA timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 47. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Table 53. SPI DC Electrical Characteristics (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

17.2 SPI AC Timing Specifications

Table 54 provides the SPI input and output AC timing specifications.

Table 54. SPI AC Timing Specifications[1]

Parameter	Symbol[2]	Min	Max	Unit
SPI outputs valid—Master mode (internal clock) delay	t_{NIKHOV}	—	6	ns
SPI outputs hold—Master mode (internal clock) delay	t_{NIKHOX}	0.5	—	ns
SPI outputs valid—Slave mode (external clock) delay	t_{NEKHOV}	—	8	ns
SPI outputs hold—Slave mode (external clock) delay	t_{NEKHOX}	2	—	ns
SPI inputs—Master mode (internal clock input setup time	t_{NIIVKH}	4	—	ns
SPI inputs—Master mode (internal clock input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50 percent level of the rising edge of CLKIN to the 50 percent level of the signal. Timings are measured at the pin.
2. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOX} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).

Figure 37 provides the AC test load for the SPI.

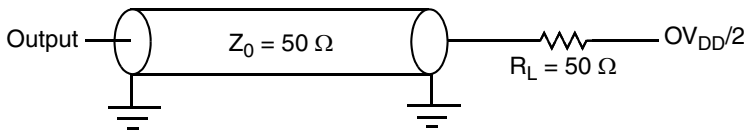
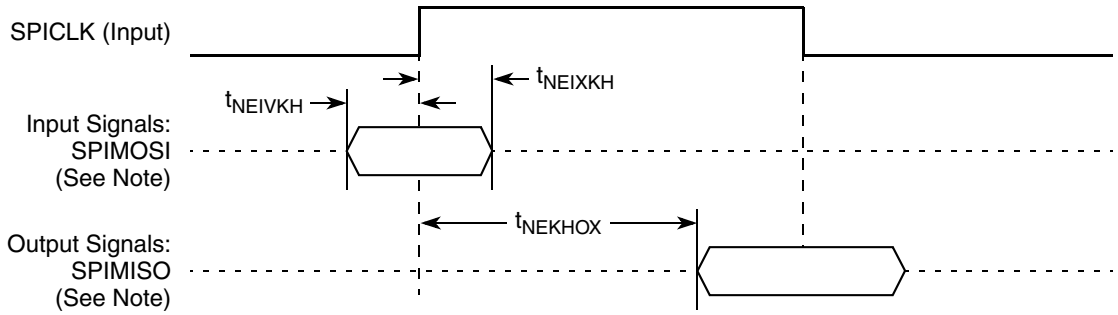


Figure 37. SPI AC Test Load

Figure 38 and Figure 39 represent the AC timings from Table 54. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

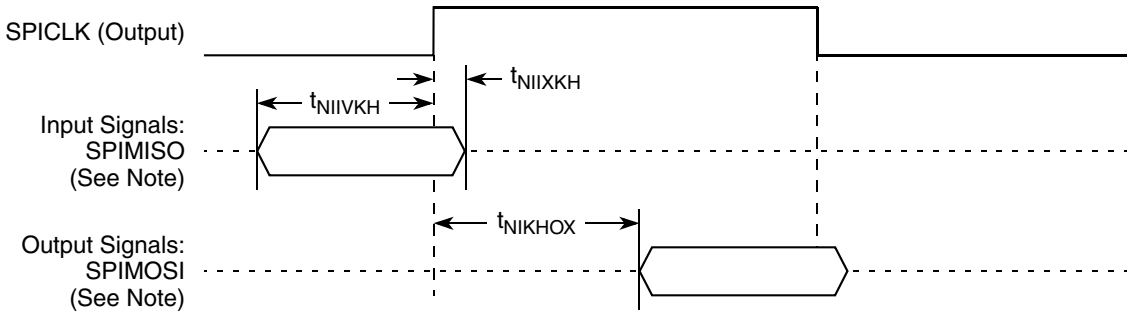
Figure 38 shows the SPI timings in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 38. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 39 shows the SPI timings in master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 39. SPI AC Timing in Master Mode (Internal Clock) Diagram

18 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8347EA is available in two packages—a tape ball grid array (TBGA) and a plastic ball grid array (PBGA). See Section 18.1, "Package Parameters for the MPC8347EA TBGA," Section 18.2, "Mechanical Dimensions for the MPC8347EA TBGA," Section 18.3, "Package Parameters for the MPC8347EA PBGA," and Section 18.4, "Mechanical Dimensions for the MPC8347EA PBGA."

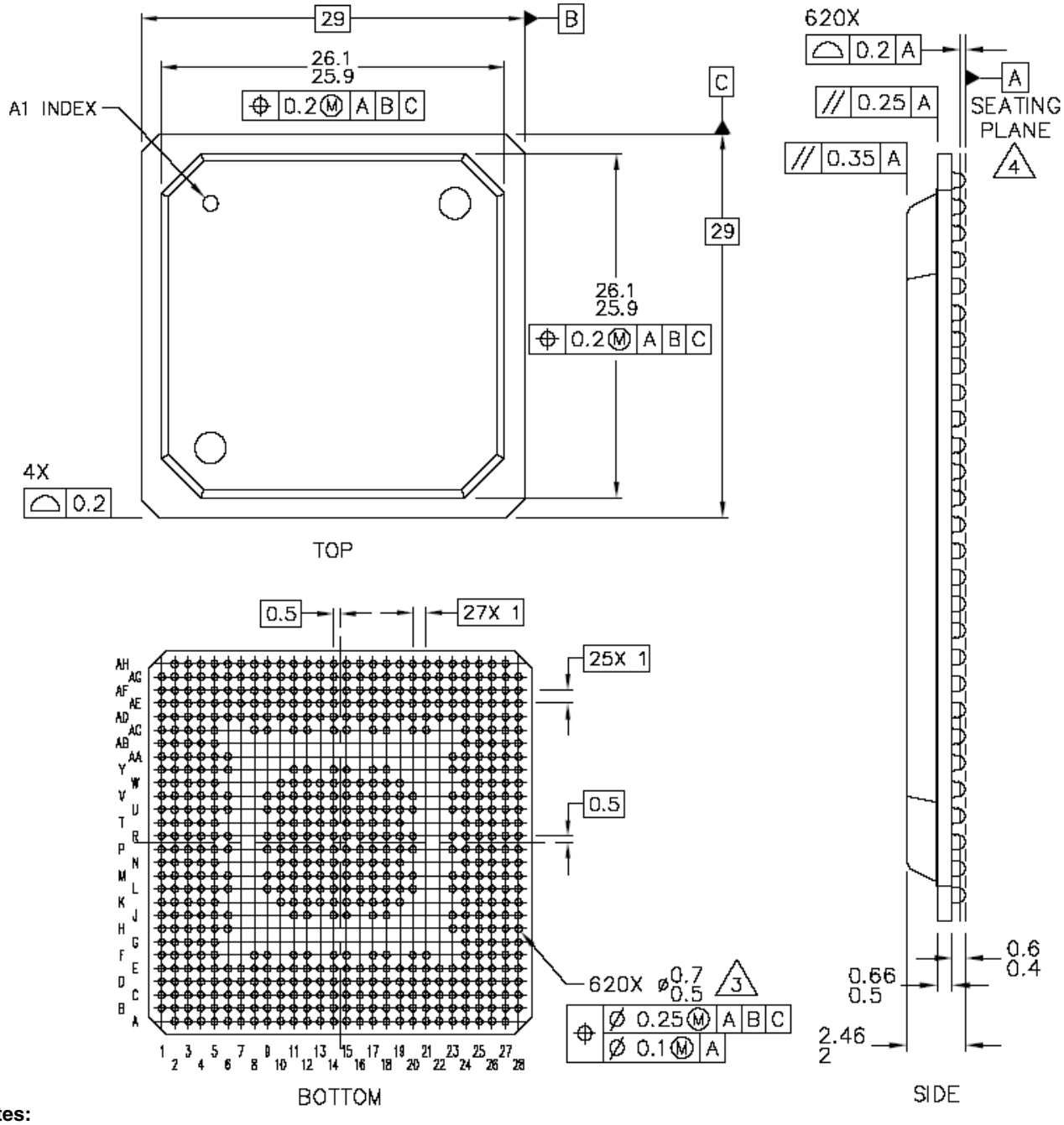
18.1 Package Parameters for the MPC8347EA TBGA

The package parameters are provided in the following list. The package type is 35 mm × 35 mm, 672 tape ball grid array (TBGA).

Package outline	35 mm × 35 mm
Interconnects	672

18.4 Mechanical Dimensions for the MPC8347EA PBGA

Figure 41 shows the mechanical dimensions and bottom surface nomenclature for the MPC8347EA, 620-PBGA package.



Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14. 5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 41. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC8347EA PBGA

Table 56. MPC8347EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MPH1_PCTL0/DR_TX_VALID_PCTL0	A26	O	OV_{DD}	—
MPH1_PCTL1/DR_TX_VALIDH_PCTL1	B25	O	OV_{DD}	—
MPH1_CLK/DR_CLK	A25	I	OV_{DD}	—
USB Port 0				
MPH0_D0_ENABLEN/DR_D8_CHGVBUS	D24	I/O	OV_{DD}	—
MPH0_D1_SER_TXD/DR_D9_DCHGVBUS	C24	I/O	OV_{DD}	—
MPH0_D2_VMO_SE0/DR_D10_DPPD	B24	I/O	OV_{DD}	—
MPH0_D3_SPEED/DR_D11_DMMD	A24	I/O	OV_{DD}	—
MPH0_D4_DP/DR_D12_VBUS_VLD	D23	I/O	OV_{DD}	—
MPH0_D5_DM/DR_D13_SESS_END	C23	I/O	OV_{DD}	—
MPH0_D6_SER_RCV/DR_D14	B23	I/O	OV_{DD}	—
MPH0_D7_DRVVBUS/DR_D15_IDPULLUP	A23	I/O	OV_{DD}	—
MPH0_NXT/DR_RX_ACTIVE_ID	D22	I	OV_{DD}	—
MPH0_DIR_DPPULLUP/DR_RESET	C22	I/O	OV_{DD}	—
MPH0_STP_SUSPEND/DR_TX_READY	B22	I/O	OV_{DD}	—
MPH0_PWRFAULT/DR_RX_VALIDH	A22	I	OV_{DD}	—
MPH0_PCTL0/DR_LINE_STATE0	E21	I/O	OV_{DD}	—
MPH0_PCTL1/DR_LINE_STATE1	D21	I/O	OV_{DD}	—
MPH0_CLK/DR_RX_VALID	C21	I	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{MCP\_OUT}}$	E8	O	OV_{DD}	2
$\overline{\text{IRQ}}$0/$\overline{\text{MCP_IN}}$/GPIO2[12]	J28	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[1:5]/GPIO2[13:17]	K25, J25, H26, L24, G27	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[6]/GPIO2[18]/CKSTOP_OUT	G28	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[7]/GPIO2[19]/CKSTOP_IN	J26	I/O	OV_{DD}	—
Ethernet Management Interface				
EC_MDC	Y24	O	LV_{DD1}	—
EC_MDIO	Y25	I/O	LV_{DD1}	11
Gigabit Reference Clock				
EC_GTX_CLK125	Y26	I	LV_{DD1}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	M26	I/O	OV_{DD}	—
TSEC1_CRS/GPIO2[21]	U25	I/O	LV_{DD1}	—
TSEC1_GTX_CLK	V24	O	LV_{DD1}	3

Table 65. Package Thermal Characteristics for TBGA (continued)

Characteristic	Symbol	Value	Unit	Notes
Junction-to-package natural convection on top	Ψ_{JT}	1	°C/W	6

Notes:
1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal, 1 m/s is approximately equal to 200 linear feet per minute (LFM).
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

Table 66 provides the package thermal characteristics for the 620 29 × 29 mm PBGA of the MPC8347EA.

Table 66. Package Thermal Characteristics for PBGA

Parameter	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection on single-layer board (1s)	$R_{\theta JA}$	21	°C/W	1, 2
Junction-to-ambient natural convection on four-layer board (2s2p)	$R_{\theta JMA}$	15	°C/W	1, 3
Junction-to-ambient (at 200 ft/min) on single-layer board (1s)	$R_{\theta JMA}$	17	°C/W	1, 3
Junction-to-ambient (at 200 ft/min) on four-layer board (2s2p)	$R_{\theta JMA}$	12	°C/W	1, 3
Junction-to-board thermal	$R_{\theta JB}$	6	°C/W	4
Junction-to-case thermal	$R_{\theta JC}$	5	°C/W	5
Junction-to-package natural convection on top	Ψ_{JT}	5	°C/W	6

Notes
1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

20.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See Table 5 for I/O power dissipation values.

20.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)
T_A = ambient temperature for the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)
T_A = ambient temperature for the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

$OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N) \div 2$.

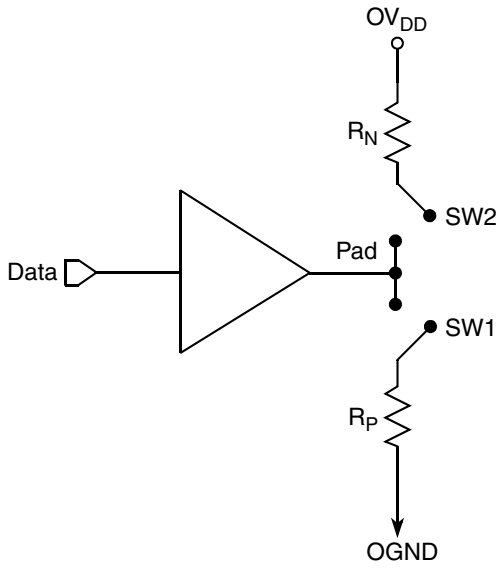


Figure 44. Driver Impedance Measurement

Two measurements give the value of this resistance and the strength of the driver current source. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term}. The measured voltage is $V_2 = (1 \div (1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1 \div V_2 - 1)$. The drive current is then $I_{source} = V_1 \div R_{source}$.

Table 69 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD}, nominal OV_{DD}, 105°C.

Table 69. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI Signals (Not Including PCI Output Clocks)	PCI Output Clocks (Including PCI_SYNC_OUT)	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	42 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	42 Target	20 Target	Z_0	W
Differential	NA	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, T_j = 105°C.

21.6 Configuration Pin Multiplexing

The MPC8347EA power-on configuration options can be set through external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see the customer-visible configuration pins). These pins are used as output only pins in normal operation.

parts including extended temperatures, refer to the device product summary page on our website listed on the back cover of this document or, contact your local Freescale sales office.

Table 70. Part Numbering Nomenclature

MPC	nnnn	e	t	pp	aa	a	r
Product Code	**Part Identifier**	**Encryption Acceleration**	**Temperature[1] Range**	**Package[2]**	**Processor Frequency[3]**	**Platform Frequency**	**Revision Level**
MPC	8347	Blank = Not included E = included	Blank = 0 to 105°C C = –40 to 105°C	ZU =TBGA VV = PB free TBGA ZQ = PBGA VR = PB Free PBGA	e300 core speed AD = 266 AG = 400 AJ = 533 AL = 667	D = 266 F = 333[4]	B = 3.1

Notes:
1. For temperature range = C, processor frequency is limited to 400 (PBGA) with a platform frequency of 266 and up to 533 (TBGA) with a platform frequency of 333
2. See Section 18, “Package and Pin Listings,” for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by Part Number Specifications may support other maximum core frequencies.
4. ALF marked parts support DDR1 data rate up to 333 MHz (at 333 MHz CSB as the 'F' marking implies) and DDR2 data rate up to 400 MHz (at 200 MHz CSB). AJF marked parts support DDR1 and DDR2 data rate up to 333 MHz (at a CSB of 333 MHz).

Table 71 shows the SVR settings by device and package type.

Table 71. SVR Settings

Device	Package	SVR (Rev. 3.0)
MPC8347EA	TBGA	8052_0030
MPC8347A	TBGA	8053_0030
MPC8347EA	PBGA	8054_0030
MPC8347A	PBGA	8055_0030

Table 72. Document Revision History (continued)

Rev. Number	Date	Substantive Change(s)
8	2/2009	• Added footnote 6 to Table 7. • In Section 9.2, "USB AC Electrical Specifications," clarified that AC table is for ULPI only. • In Table 39, corrected t_{LBKHOV} parameter to t_{LBKLOV} (output data is driven on falling edge of clock in DLL bypass mode). Similarly, made the same correction to Figure 22, Figure 24, and Figure 25 for output signals. • Added footnote 10 and 11 to Table 55 and Table 56. • In Section 21.1, "System Clocking," removed "(AVDD1)" and "(AVDD2") from bulleted list. • In Section 21.2, "PLL Power Supply Filtering," in the second paragraph, changed "provide five independent filter circuits," and "the five AVDD pins" to provide four independent filter circuits," and "the four AVDD pins." • In Table 58, corrected the max csb_clk to 266 MHz. • In Table 64, added PLL configurations 903, 923, A03, A23, and 503 for 533 MHz • Added footnote 4 to Table 70. • In Table 70, updated note 1 to say the following: "For temperature range = C, processor frequency is limited to 533 (TBGA) and 400 (PBGA) with a platform frequency of 266."
7	4/2007	• In Table 3, "Output Drive Capability," changed the values in the Output Impedance column and added USB to the seventh row. • In Table 4, "Operating Frequencies for TBGA," added column for 400 MHz. • In Section 21.7, "Pull-Up Resistor Requirements,"deleted last two paragraphs and after first paragraph, added a new paragraph. • Deleted Section 21.8, "JTAG Configuration Signals," and Figure 43, "JTAG Interface Connection."
6	3/2007	• Page 1, updated first paragraph to reflect PowerQUICC II Pro information. • In Table 18, "DDR and DDR2 SDRAM Input AC Timing Specifications," added note 2 to t_{CISKEW} and deleted original note 3; renumbered the remaining notes. • In Figure 43, "JTAG Interface Connection," updated with new figure. • In Table 57, "Operating Frequencies for TBGA," in the 'Coherent system bus frequency (*csb_clk*)' row, changed the value in the 533 MHz column to 100-333. • In Table 63, "Suggested PLL Configurations," under the subhead, '33 MHz CLKIN/PCI_CLK Options,' added row A03 between Ref. No. 724 and 804. Under the subhead '66 MHz CLKIN/PCI_CLK Options,' added row 503 between Ref. No. 305 and 404. For Ref. No. 306, changed the CORE PLL value to 0000110. • In Section 23, "Ordering Information," replaced first paragraph and added a note. • In Section 23.1, "Part Numbers Fully Addressed by this Document," replaced first paragraph.
5	1/2007	• In Table 1, "Absolute Maximum Ratings," added (1.36 max for 667-MHz core frequency). • In Table 2, "Recommended Operating Conditions," added a row showing nominal core supply voltage of 1.3 V for 667-MHz parts. • In Table 4, "MPC8347EA Power Dissipation," added two footnotes to 667-MHz row showing nominal core supply voltage of 1.3 V for 667-MHz parts. • In Table 54, "MPC8347EA (TBGA) Pinout Listing," updated V_{DD} row to show nominal core supply voltage of 1.3 V for 667-MHz parts.
4	12/2006	Table 19, "DDR and DDR2 SDRAM Output AC Timing Specifications," modified T_{ddkhds} for 333 MHz from 900 ps to 775 ps.
3	11/2006	• Updated note in introduction. • In the features list in Section 1, "Overview," updated DDR data rate to show 266 MHz for PBGA parts for all silicon revisions, and 400 MHz for DDR2 for TBGA parts for silicon Rev. 2 and 3. • In Table 5, "MPC8347EA Typical I/O Power Dissipation," added GV_{DD} 1.8-V values for DDR2; added table footnote to designate rates that apply only to the TBGA package. • In Section 23, "Ordering Information," replicated note from document introduction.

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